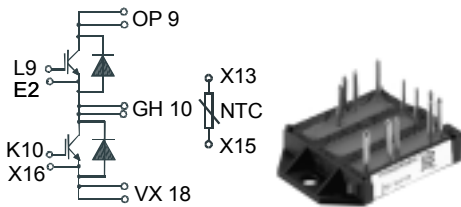


IGBT Module

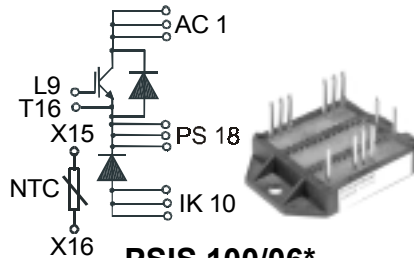
Preliminary Data Sheet

PSIG 100/06
PSI 100/06*
PSIS 100/06*
PSSI 100/06*

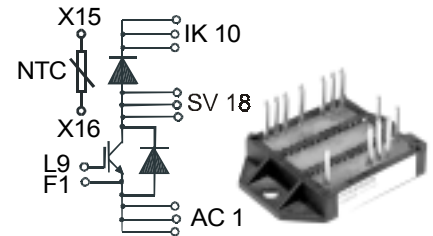
I_{C25} = 93 A
 V_{CES} = 600 V
 $V_{CE(sat)typ.}$ = 2.4 V



PSI 100/06*



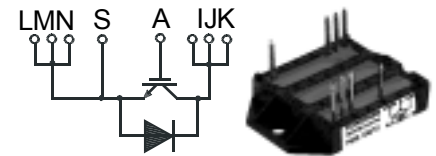
PSIS 100/06*



PSSI 100/06*

IGBTs

Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	600	V
V_{GES}		± 20	V
I_{C25}	$T_C = 25^{\circ}\text{C}$	93	A
I_{C80}	$T_C = 80^{\circ}\text{C}$	63	A
I_{CM} V_{CEK}	$V_{GE} = \pm 15\text{ V}; R_G = 15\ \Omega; T_{VJ} = 125^{\circ}\text{C}$ RBSOA, Clamped inductive load; $L = 100\ \mu\text{H}$	150	A
		V_{CES}	
t_{SC} (SCSOA)	$V_{CE} = V_{CES}; V_{GE} = \pm 15\text{ V}; R_G = 15\ \Omega; T_{VJ} = 125^{\circ}\text{C}$ non-repetitive	10	μs
P_{tot}	$T_C = 25^{\circ}\text{C}$	294	W



PSIG 100/06

*NTC optional

Features

- Package with DCB ceramic base plate
- Isolation voltage 3000 V~
- Planar glass passivated chips
- Low forward voltage drop
- Leads suitable for PC board soldering
- UL registered, E 148688

Applications

- AC and DC motor control
- AC servo and robot drives
- power supplies
- welding inverters

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling capability
- High power density
- Small and light weight

Symbol	Conditions	Characteristic Values ($T_{VJ} = 25^{\circ}\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{CE(sat)}$	$I_C = 100\text{ A}; V_{GE} = 15\text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	2.4	2.8	V
$V_{GE(th)}$	$I_C = 1.5\text{ mA}; V_{GE} = V_{CE}$	4.5		6.5 V
I_{CES}	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		1.4	6.5 mA
I_{GES}	$V_{CE} = 0\text{ V}; V_{GE} = \pm 20\text{ V}$			150 nA
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off}	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 300\text{ V}; I_C = 60\text{ A}$ $V_{GE} = 15/0\text{ V}; R_G = 15\ \Omega$	150		ns
		60		ns
		450		ns
		40		ns
		3.2		mJ
		2.2		mJ
C_{ies}	$V_{CE} = 25\text{ V}; V_{GE} = 0\text{ V}; f = 1\text{ MHz}$	4.2		nF
R_{thJC} R_{thJH}	(per IGBT) with heatsink compound (0.42 K/m.K; 50 μm)	0.85		0.43 K/W K/W

Caution: These Devices are sensitive to electrostatic discharge. Users should observe proper ESD handling precautions.

